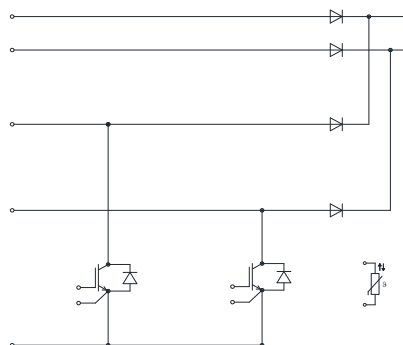
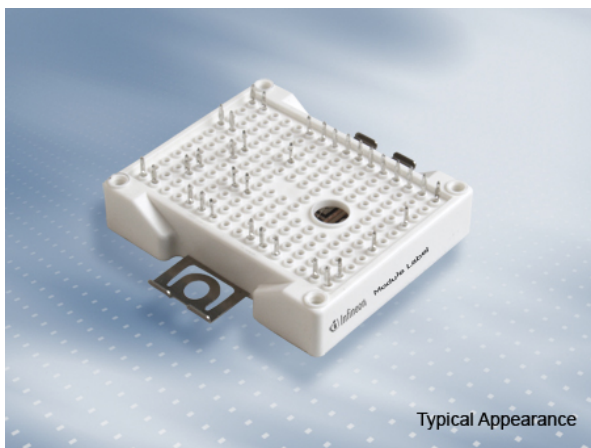


初步数据 / Preliminary Data



$V_{CES} = 1200V$
 $I_{C\ nom} = 80A / I_{CRM} = 160A$

典型应用

- 太阳能应用
- UPS系统

电气特性

- 高速IGBT H3
- 低开关损耗

机械特性

- 低热阻的三氧化二铝 (Al_2O_3 衬底
- 集成NTC温度传感器
- 紧凑型设计
- PressFIT 压接技术

Typical Applications

- Solar Applications
- UPS Systems

Electrical Features

- High Speed IGBT H3
- Low Switching Losses

Mechanical Features

- Al_2O_3 Substrate with Low Thermal Resistance
- Integrated NTC temperature sensor
- Compact design
- PressFIT Contact Technology

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

| Content of the Code | Digit |
|----------------------------|---------|
| Module Serial Number | 1 - 5 |
| Module Material Number | 6 - 11 |
| Production Order Number | 12 - 19 |
| Datecode (Production Year) | 20 - 21 |
| Datecode (Production Week) | 22 - 23 |

| | | |
|-----------------|---------------------------------|----------------------|
| prepared by: CM | date of publication: 2013-11-11 | |
| approved by: MB | revision: 2.0 | UL approved (E83335) |

初步数据
Preliminary Data

旁路二极管 / Bypass-Diode

最大额定值 / Maximum Rated Values

| | | | | |
|---|---|------------------|-------------|--------------------------------------|
| 反向重复峰值电压 Repetitive peak reverse voltage | $T_{vj} = 25^{\circ}\text{C}$ | V_{RRM} | 1200 | V |
| 最大正向均方根电流(每芯片) Maximum RMS forward current per chip | $T_c = 80^{\circ}\text{C}$ | I_{FRMSM} | 50 | A |
| 最大整流器输出均方根电流 Maximum RMS current at rectifier output | $T_c = 80^{\circ}\text{C}$ | I_{RMSM} | 60 | A |
| 正向浪涌电流 Surge forward current | $t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$ | I_{FSM} | 450 360 | A A |
| I ² t-值 I ² t - value | $t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$ | I ² t | 1000 650 | A ² s A ² s |

特征值 / Characteristic Values

| | | | min. | typ. | max. | |
|--|---|--------------------|------|------|------|--------------------|
| 正向电压 Forward voltage | $T_{vj} = 150^{\circ}\text{C}, I_F = 30\text{ A}$ | V_F | | 0,95 | | V |
| 反向电流 Reverse current | $T_{vj} = 150^{\circ}\text{C}, V_R = 1200\text{ V}$ | I_R | | 0,10 | | mA |
| 结 - 外壳热阻 Thermal resistance, junction to case | 每个二极管 / per diode | R_{thJC} | | 0,80 | 1,05 | K/W |
| 外壳 - 散热器热阻 Thermal resistance, case to heatsink | 每个二极管 / per diode $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$ | R_{thCH} | | 0,80 | | K/W |
| 在开关状态下温度 Temperature under switching conditions | | $T_{vj\text{ op}}$ | | | | $^{\circ}\text{C}$ |

反极性保护二极管A / Inverse-polarity protection diode A

最大额定值 / Maximum Rated Values

| | | | | |
|---|---|------------------|------------|--------------------------------------|
| 反向重复峰值电压 Repetitive peak reverse voltage | $T_{vj} = 25^{\circ}\text{C}$ | V_{RRM} | 1200 | V |
| 最大正向均方根电流(每芯片) Maximum RMS forward current per chip | $T_c = 80^{\circ}\text{C}$ | I_{FRMSM} | 30 | A |
| 最大整流器输出均方根电流 Maximum RMS current at rectifier output | $T_c = 80^{\circ}\text{C}$ | I_{RMSM} | 60 | A |
| 正向浪涌电流 Surge forward current | $t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$ | I_{FSM} | 290 245 | A A |
| I ² t-值 I ² t - value | $t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$ | I ² t | 420 300 | A ² s A ² s |

特征值 / Characteristic Values

| | | | min. | typ. | max. | |
|--|---|--------------------|------|------|------|--------------------|
| 正向电压 Forward voltage | $T_{vj} = 150^{\circ}\text{C}, I_F = 20\text{ A}$ | V_F | | 1,00 | | V |
| 反向电流 Reverse current | $T_{vj} = 150^{\circ}\text{C}, V_R = 1200\text{ V}$ | I_R | | 0,10 | | mA |
| 结 - 外壳热阻 Thermal resistance, junction to case | 每个二极管 / per diode | R_{thJC} | | 1,20 | 1,35 | K/W |
| 外壳 - 散热器热阻 Thermal resistance, case to heatsink | 每个二极管 / per diode $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$ | R_{thCH} | | 1,15 | | K/W |
| 在开关状态下温度 Temperature under switching conditions | | $T_{vj\text{ op}}$ | | | | $^{\circ}\text{C}$ |

| | |
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